


**General Description:**

- (1) Chip Dimension  
 Chip Size= 6 mil x 8 mil (170um x 220um)  
 Chip Thickness = 90±10 μm  
 P/N Bonding Pad = 70±5 μm
- (2) Electrode:  
 P (Anode) → Au  
 N (Cathode) → Au
- (3) Structure:  
 Refer to drawing  
 SiO<sub>2</sub> Passivated surface

**Electro-optical Characteristics(Ta=RT)**

| Parameter           | Symbol         | Min. | Typ. | Max. | Unit | Condition            |
|---------------------|----------------|------|------|------|------|----------------------|
| Forward Voltage     | V <sub>F</sub> | 2.7  | -    | 3.0  | V    | I <sub>F</sub> = 5mA |
| Dominant Wavelength | λ <sub>D</sub> | 450  | -    | 470  | nm   | I <sub>F</sub> = 5mA |
| Reverse Current     | I <sub>R</sub> | 0    | -    | 2    | μA   | V <sub>R</sub> =-5V  |

| 亮度<br>Luminous<br>Intensity( I <sub>v</sub> )<br>mcd at<br>I <sub>F</sub> =5mA | 波長 Dominant Wavelength(nm) |           |           |           |           |           |           |           |           |
|--|----------------------------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|
|  | Range                      | 450~452.5 | 452.5~455 | 455~457.5 | 457.5~460 | 460~462.5 | 462.5~465 | 465~467.5 | 467.5~470 |
| 5~10   |                            |           |           |           |           |           |           |           |           |
| 10~15  |                            |           |           |           |           |           |           |           |           |
| 15~20  |                            |           |           |           |           |           |           |           |           |
| 20~25  |                            |           |           |           |           |           |           |           |           |
| 25~30  |                            |           |           |           |           |           |           |           |           |
| 30~35  |                            |           |           |           |           |           |           |           |           |
| 35~40  |                            |           |           |           |           |           |           |           |           |

**Features:**

1. High Luminous Intensity
2. Long Operation Life
3. High Current; Pulse Operation
4. Indoor/Outdoor Applications

**Notes:**

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD